



## PRODUCT DATA SHEET



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**Datasheet**



**Resources**



**Samples**

Please note: Please check the JINGAO Semiconductor website to verify the updated device numbers. The most current and up-to-date ordering information can be found at [www.jg-semi.cn](http://www.jg-semi.cn). Please email any questions regarding the system integration to [JINGAO\\_questions@jgsemi.com](mailto:JINGAO_questions@jgsemi.com).

## General Description

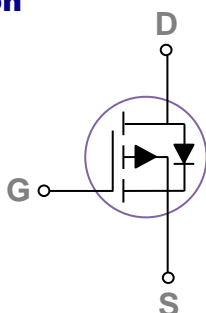
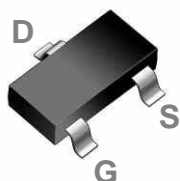
These P-Channel enhancement mode power field effect transistors are using trench DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency fast switching applications.

BVDSS	RDS(ON)	ID
-60V	160mΩ	-2A

## Features

- -60V, -2A,  $R_{DS(ON)} = 160m\Omega @ V_{GS} = -10V$
- Improved  $dv/dt$  capability
- Fast switching
- Green Device Available

## SOT23-3 Pin Configuration



## Applications

- Motor Drive
- Power Tools
- LED Lighting

## Absolute Maximum Ratings $T_c=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Rating	Units
$V_{DS}$	Drain-Source Voltage	-60	V
$V_{GS}$	Gate-Source Voltage	$\pm 20$	V
$I_D$	Drain Current – Continuous ( $T_A=25^\circ\text{C}$ )	-2	A
	Drain Current – Continuous ( $T_A=70^\circ\text{C}$ )	-1.6	A
$I_{DM}$	Drain Current – Pulsed <sup>1</sup>	-8	A
$P_D$	Power Dissipation ( $T_A=25^\circ\text{C}$ )	1.56	W
	Power Dissipation – Derate above $25^\circ\text{C}$	0.012	W/ $^\circ\text{C}$
$T_{STG}$	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
$T_J$	Operating Junction Temperature Range	-55 to 125	$^\circ\text{C}$

## Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction to ambient	---	80	$^\circ\text{C/W}$

**Electrical Characteristics (T<sub>J</sub>=25 °C, unless otherwise noted)**
**Off Characteristics**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =-250uA	-60	---	---	V
△BV <sub>DSS</sub> /△T <sub>J</sub>	BV <sub>DSS</sub> Temperature Coefficient	Reference to 25°C, I <sub>D</sub> =-1mA	---	-0.05	---	V/°C
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> =-60V, V <sub>GS</sub> =0V, T <sub>J</sub> =25°C	---	---	-1	uA
		V <sub>DS</sub> =-48V, V <sub>GS</sub> =0V, T <sub>J</sub> =125°C	---	---	-10	uA
I <sub>GSS</sub>	Gate-Source Leakage Current	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	---	---	±100	nA

**On Characteristics**

R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance	V <sub>GS</sub> =-10V, I <sub>D</sub> =-2A	---	160	200	mΩ
		V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-1.5A	---	200	240	mΩ
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>GS</sub> =V <sub>DS</sub> , I <sub>D</sub> =-250uA	-1.0	-1.9	-2.5	V
△V <sub>GS(th)</sub>	V <sub>GS(th)</sub> Temperature Coefficient		---	5	---	mV/°C
g <sub>fs</sub>	Forward Transconductance	V <sub>DS</sub> =-10V, I <sub>D</sub> =-2A	---	3.5	---	S

**Dynamic and switching Characteristics**

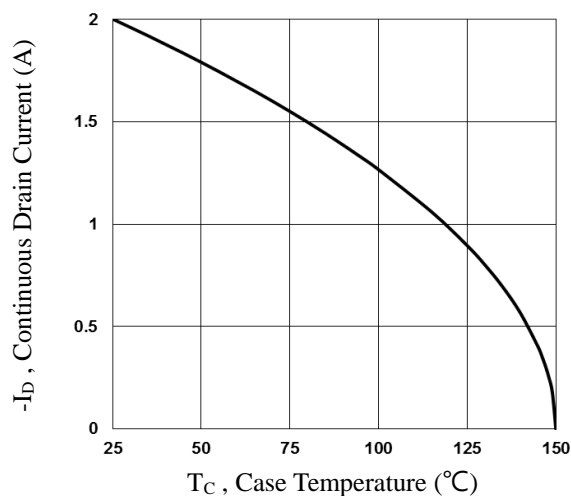
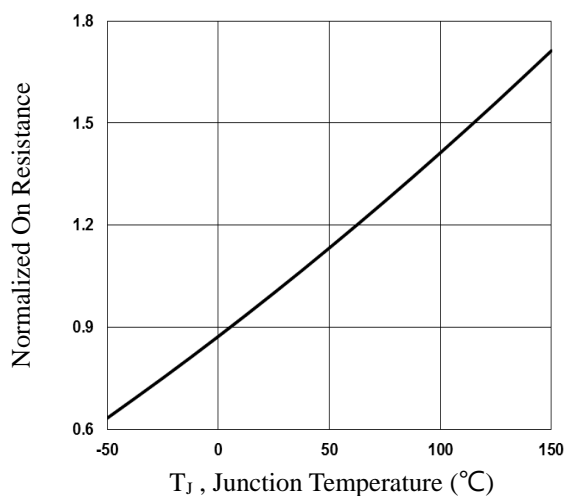
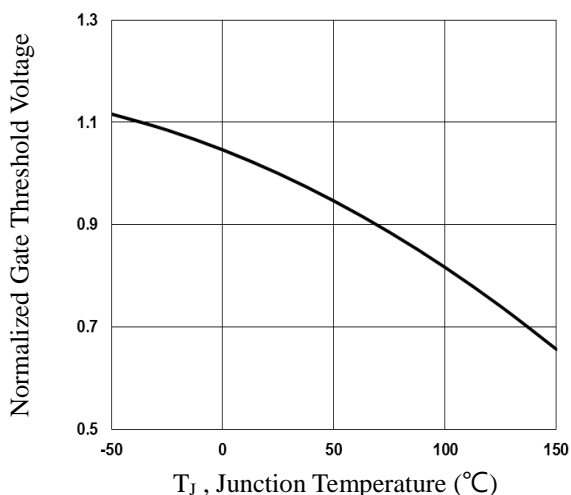
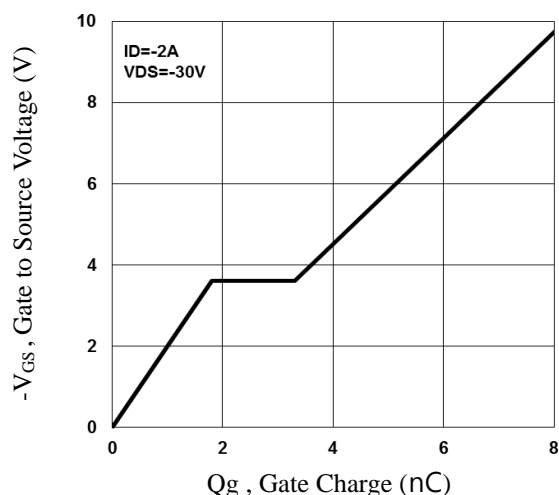
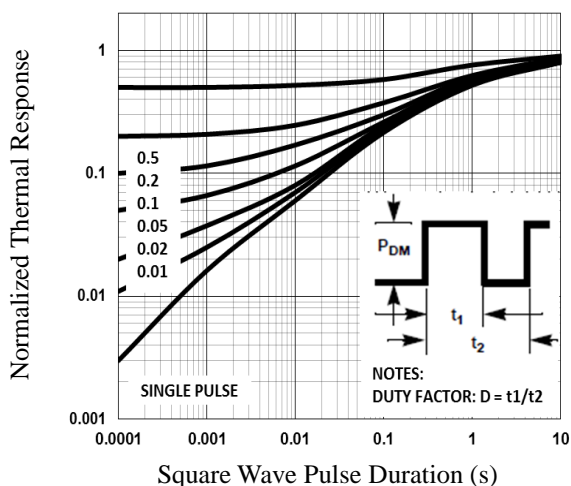
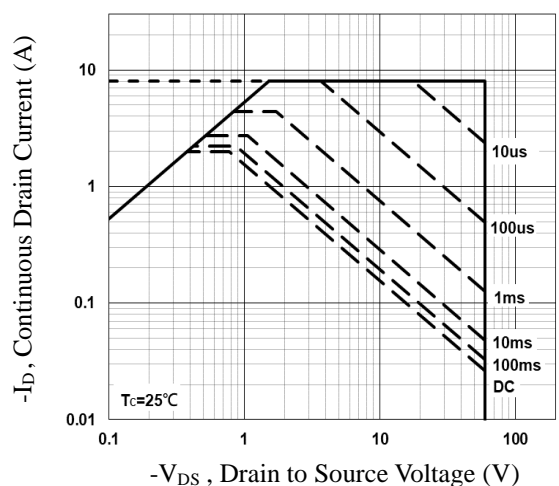
Q <sub>g</sub>	Total Gate Charge <sup>2, 3</sup>	V <sub>DS</sub> =-30V, V <sub>GS</sub> =-10V, I <sub>D</sub> =-2A	---	8.2	---	nC
Q <sub>gs</sub>	Gate-Source Charge <sup>2, 3</sup>		---	1.8	---	
Q <sub>gd</sub>	Gate-Drain Charge <sup>2, 3</sup>		---	1.5	---	
T <sub>d(on)</sub>	Turn-On Delay Time <sup>2, 3</sup>	V <sub>DD</sub> =-30V, V <sub>GS</sub> =-10V, R <sub>G</sub> =6Ω I <sub>D</sub> =-1A	---	5.2	---	ns
T <sub>r</sub>	Rise Time <sup>2, 3</sup>		---	19	---	
T <sub>d(off)</sub>	Turn-Off Delay Time <sup>2, 3</sup>		---	35	---	
T <sub>f</sub>	Fall Time <sup>2, 3</sup>		---	10.6	---	
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> =-30V, V <sub>GS</sub> =0V, F=1MHz	---	425	---	pF
C <sub>oss</sub>	Output Capacitance		---	35	---	
C <sub>rss</sub>	Reverse Transfer Capacitance		---	20	---	

**Drain-Source Diode Characteristics and Maximum Ratings**

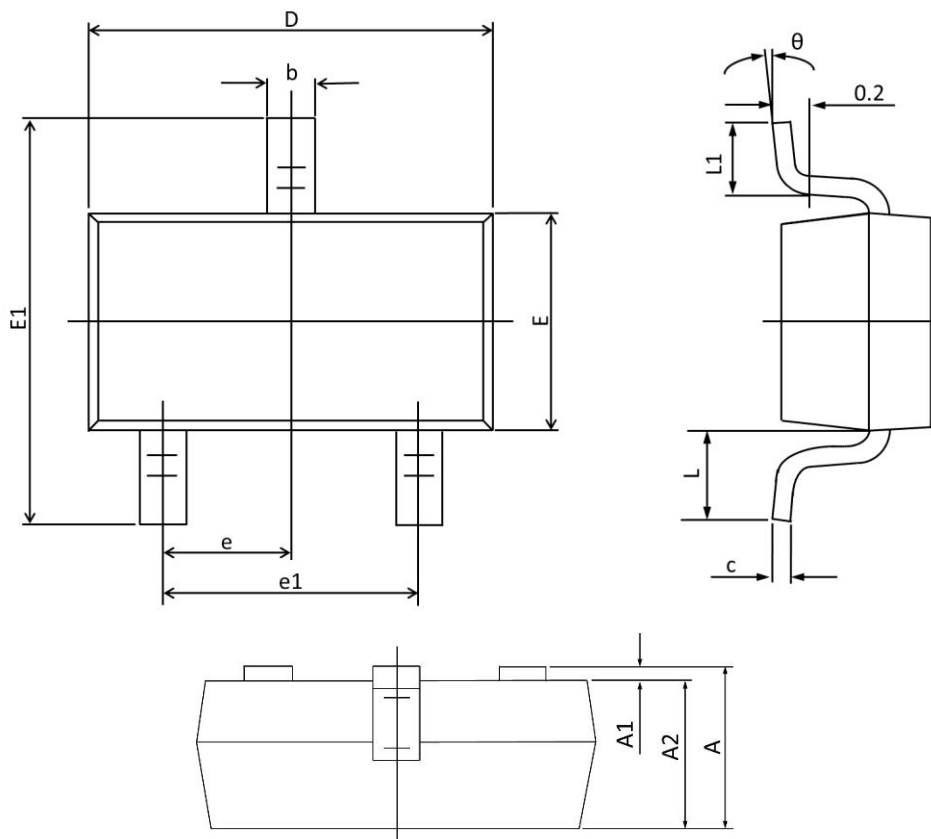
Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I <sub>S</sub>	Continuous Source Current	V <sub>G</sub> =V <sub>D</sub> =0V, Force Current	---	---	-2	A
I <sub>SM</sub>	Pulsed Source Current		---	---	-4	A
V <sub>SD</sub>	Diode Forward Voltage	V <sub>GS</sub> =0V, I <sub>S</sub> =-1A, T <sub>J</sub> =25°C	---	---	-1.2	V

Note :

1. Repetitive Rating : Pulsed width limited by maximum junction temperature.
2. The data tested by pulsed, pulse width ≤ 300us, duty cycle ≤ 2%.
3. Essentially independent of operating temperature.


**Fig.1 Continuous Drain Current vs.  $T_c$** 

**Fig.2 Normalized  $R_{DS(on)}$  vs.  $T_J$** 

**Fig.3 Normalized  $V_{th}$  vs.  $T_J$** 

**Fig.4 Gate Charge Waveform**

**Fig.5 Normalized Transient Impedance**

**Fig.6 Maximum Safe Operation Area**

## SOT23-3 PACKAGE INFORMATION



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.050	1.450	0.041	0.057
A1	---	0.150	---	0.006
A2	0.900	1.300	0.035	0.051
b	0.300	0.490	0.012	0.019
c	0.100	0.200	0.004	0.008
D	2.820	3.050	0.111	0.120
E	1.500	1.750	0.059	0.069
E1	2.600	3.000	0.102	0.118
e	0.950 TYP.		0.037 TYP.	
e1	1.800	2.000	0.071	0.079
L	0.700 REF.		0.028 REF.	
L1	0.300	0.600	0.012	0.024
θ	0°	8°	0°	8°

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